

IN THE CLAIMS:

Please amend the claims as follows:

1. (currently amended) A process for forming a dielectric film on an exposed surface of a layer containing silicon in a chamber, ~~said the~~ process comprising:
determining ~~the a~~ desired thickness of ~~a layer of said the~~ dielectric film, ~~said the~~ dielectric film including silicon dioxide and silicon nitride therein when formed on ~~said the~~ exposed surface of ~~said the~~ layer containing silicon when the layer is maintained at a temperature in the range of at least 600° C to 1100° C in an oxidizing atmosphere;
[heating said exposed surface of said layer containing silicon to a temperature in the range of at least 600° C ~~and to~~ 1100° C;]
introducing into [providing] the chamber a gaseous mixture including nitrous oxide exhibiting a partial pressure, ozone exhibiting a partial pressure, at least one compound containing a halogen selected from the group consisting of Cl₂, Br₂, HCl and HBr, and steam, the partial pressure of the ozone being at least one tenth the partial pressure of the nitrous oxide in the gaseous mixture, the gaseous mixture being substantially free of fluorine-containing gases; and
forming the dielectric film of the desired thickness by contacting [subjecting] ~~said the~~ exposed surface of ~~a the~~ layer containing silicon with [to] the gaseous mixture including ~~at least~~ nitrous oxide, ozone, at least one compound containing a halogen selected from the group consisting of Cl₂, Br₂, HCl and HBr, and steam [for a period sufficient to form the dielectric film to the desired thickness].
2. (currently amended) The process of claim 1, wherein ~~said the~~ chamber is sealed.
3. (currently amended) The process of claim 2, wherein ~~said the~~ chamber is maintained at a pressure within a range of 1 to 7,600 torr.

4. (currently amended) A process for forming a field-effect transistor gate dielectric layer on an exposed surface of a layer of polycrystalline silicon having a desired thickness in a chamber, ~~said the~~ process comprising:

determining the desired thickness of ~~a layer of said the~~ field-effect transistor gate dielectric ~~film, aid dielectric film~~ layer, the field-effect transistor gate dielectric layer containing silicon dioxide and silicon nitride when formed on ~~said the~~ exposed surface of ~~said the~~ layer ~~containing of polycrystalline silicon~~ when the layer is maintained at a temperature in the range of at least 600° C to 1100° C in an oxidizing atmosphere;

[heating ~~said the~~ exposed surface of ~~said the~~ layer of polycrystalline silicon to a temperature in the range of at least 600° C to 1100° C;]

providing a gaseous mixture including nitrous oxide, ozone, at least one compound containing a halogen selected from the group consisting of Cl₂, Br₂, HCl and HBr, and steam, the gaseous mixture being substantially free of fluorine-containing gases; and

forming the field-effect transistor gate dielectric to the desired thickness by ~~subjecting said the~~ exposed surface of ~~said the~~ layer of polycrystalline silicon to the gaseous mixture, the gaseous mixture including nitrous oxide ~~gas~~ at a partial pressure and ozone ~~gas~~ at a partial pressure, the partial pressure of the ozone ~~gas~~ being at least one tenth the partial pressure of the nitrous oxide[, for a period sufficient to form ~~said the~~ field-effect transistor gate dielectric layer to the desired thickness].

5. (currently amended) The process of claim 4, wherein ~~said the~~ chamber is sealed.

6. (currently amended) The process of claim 4, wherein ~~said the~~ chamber is maintained at a pressure within a range of 1 to 7,600 torr.